Dual D Flip-Flop with Set and Reset with LSTTL Compatible Inputs

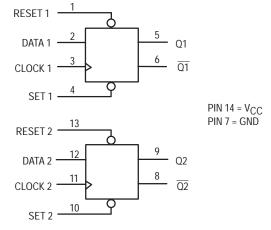
High-Performance Silicon-Gate CMOS

The MC74HCT74A is identical in pinout to the LS74. This device may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

This device consists of two D flip–flops with individual Set, Reset, and Clock inputs. Information at a D–input is transferred to the corresponding Q output on the next positive going edge of the clock input. Both Q and \overline{Q} outputs are available from each flip–flop. The Set and Reset inputs are asynchronous.

- Output Drive Capability: 10 LSTTL Loads
- TTL NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 136 FETs or 34 Equivalent Gates

LOGIC DIAGRAM



Design Criteria	Value	Units
Internal Gate Count*	34	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рЈ

^{*}Equivalent to a two-input NAND gate.

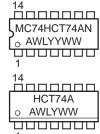


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PDIP-14 N SUFFIX CASE 646



MARKING

DIAGRAMS

SOIC-14 D SUFFIX CASE 751A

A = Assembly Location
WL or L = Wafer Lot

YY or Y = Year WW or W = Work Week

PIN ASSIGNMENT

RESET 1	1 •	14	v _{cc}
DATA 1	2	13	RESET 2
CLOCK 1	3	12	DATA 2
SET 1	4	11	CLOCK 2
Q1 [5	10	SET 2
Q1 [6	9	Q2
GND [7	8	02

FUNCTION TABLE

	Inp	Out	puts		
Set	Reset	Clock	Data	Q	Q
L	Н	Х	Χ	Н	L
Н	L	X	Χ	L	Н
L	L	X	Χ	H*	H*
Н	Н		Н	Н	L
Н	Н		L	L	Н
Н	Н	L	X	No Cl	hange
Н	Н	Н	Χ	No Cl	hange
Н	Н	~	Χ	No Cl	hange

*Both outputs will remain high as long as Set and Reset are low, but the output states are unpredictable if Set and Reset go high simultaneously.

ORDERING INFORMATION

Device	Package	Shipping
MC74HCT74AN	PDIP-14	2000 / Box
MC74HCT74AD	SOIC-14	55 / Rail
MC74HCT74ADR2	SOIC-14	2500 / Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
lin	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: -7mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
Vcc	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 4.0 \text{ mA}$	4.5	3.98	3.84	3.7	
VOL	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 4.0 \text{ mA}$	4.5	0.26	0.33	0.4	
lin	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	2.0	20	80	μА

∆ICC	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ –55 °C	25°C to 125°C	
	Ouncil	$I_{\text{out}} = 0 \mu\text{A}$	5.5	2.9	2.4	mA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: -10mW/°C from 65° to 125°C

AC ELECTRICAL CHARACTERISTICS (V $_{CC}$ = 5.0 V \pm 10%, C $_{L}$ = 50 pF, Input t $_{r}$ = t $_{f}$ = 6.0 ns)

		Guaranteed Limit		nit	
Symbol	Parameter	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
fmax	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	30	24	20	MHz
tPLH, tPHL	Maximum Propagation Delay, Clock to Q or $\overline{\mathbb{Q}}$ (Figures 1 and 4)	24	30	36	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Set or Reset to Q or \overline{Q} (Figures 2 and 4)	24	30	36	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	15	19	22	ns
C _{in}	Maximum Input Capacitance	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

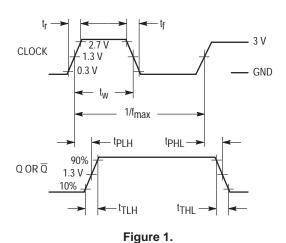
		Typical @ 25°C, V _{CC} = 5.0 V	
CPE	Power Dissipation Capacitance (Per Enabled Output)*	32	pF

^{*}Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (V_{CC} = 5.0 V \pm 10%, C_L = 50 pF, Input t_f = t_f = 6.0 ns)

			Guarante		eed Limit							
			– 55 to 25°C				· · · · ·		5°C	≤ 12	25°C	
Symbol	Parameter	Fig.	Min	Max	Min	Max	Min	Max	Units			
t _{su}	Minimum Setup Time, Data to Clock	3	15		19		22		ns			
th	Minimum Hold Time, Clock to Data	3	3		3		3		ns			
t _{rec}	Minimum Recovery Time, Set or Reset Inactive to Clock	2	6		8		9		ns			
t _W	Minimum Pulse Width, Clock	1	15		19		22		ns			
t _W	Minimum Pulse Width, Set or Reset	2	15		19		22		ns			
t _r , t _f	Maximum Input Rise and Fall Times	1		500		500		500	ns			

SWITCHING WAVEFORMS



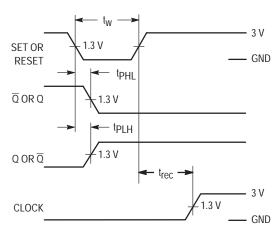


Figure 2.

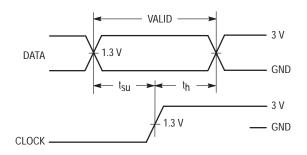
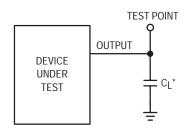
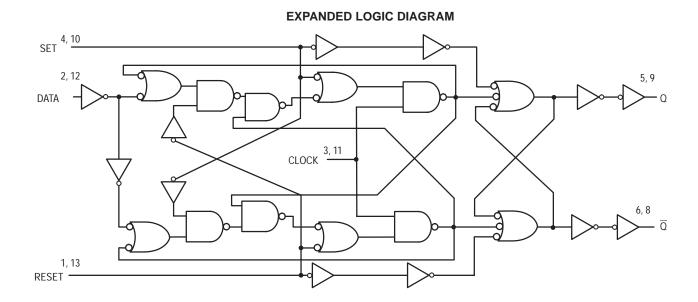


Figure 3.



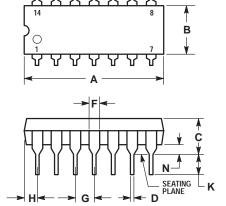
*Includes all probe and jig capacitance

Figure 4.



PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 ISSUE L



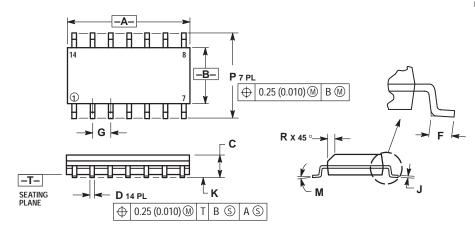


- NOTES:
 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE
 POSITION AT SEATING PLANE AT MAXIMUM
 MATERIAL CONDITION.
 2. DIMENSION L TO CENTER OF LEADS WHEN
 FORMED PARALLEL.
 3. DIMENSION B DOES NOT INCLUDE MOLD

 - FLASH.
 4. ROUNDED CORNERS OPTIONAL

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300	BSC	7.62 BSC	
M	0 °	10°	0°	10°
N	0.015	0.039	0.39	1 01

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE F



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- 1. DIMENSIONING AND TOLERANCING PER ANS Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWARD E DAMBAR.
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
D	0.25	0.50	0.010	0.010

Notes

Notes

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